Hall Ticket No.:												Set-1
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## Course Code: 23MTVLE06 MALINENI LAKSHMAIAH WOMEN'S ENGINEERING COLLEGE

(AUTONOMOUS)

I - M.Tech. I - Semester (MR23) Regular Examinations, March - 2024

**PHOTONICS** 

**Department of Electronics & Communication Engineering** 

Time: 3 hours

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Max. Marks: 75

## Answer **ALL** the questions – **5\*15=75 Marks**

Q. No.		Question	Marks	со	BL
-	a)	With neat sketch explain Semiconductor optical amplifiers	7M	CO1	L3
L	b)	Explain the construction geometry of free electron laser system	8M	CO1	L3
2	a)	Illustrate the forward and backward pumping capability associated with the Raman Amplifier.	8M	CO1	L3
	b)	Explain application of Lasers in Isotope separation	7M	CO1	L3

3	a	Differentiate Active Mode Locking and Passive Mode Locking.	8M	CO2	L3
	b	Explain any two Methods of Q- switching.	7M	CO2	L3
(OR)					
4	a	Explain why it is unwise to place the Q-switch in a Q-switched laser between the gain medium and the output mirror of the resonator	8M	CO2	L3
	b	Define and explain the terms: Frequency doubling and Phase conjugation	7M	CO2	L3

5	а	Discuss about LED materials, Device configuration and efficiency	7M	CO3	L4
	b	The total efficiency of an injection laser with a GaAs active region is 20%. Thevoltage applied to the device is 3.5 V and the band gap energy for GaAs is 1.4 eV.Calculate the external power efficiency of the device	8M	CO3	L4
(OR)					
6	а	Discuss the requirement for population inversion in order that stimulated emissionmay dominate over spontaneous emission. Illustrate with an energy level diagram of a common non- semiconductor laser.	8M	CO3	L4
	b	Discuss about Injection efficiency, Internal quantum efficiency of optical source.	7M	CO3	L3

	a	Outline the common LED structures for optical fiber communications, discuss theirrelative merits and drawbacks	7M	CO4	L3
		A planar LED is fabricated from gallium arsenide which has a refractive index of 3.			
7		(i) Calculate the optical power emitted into air as a percentage of the internaloptical power for the device when the transmission factor at the crystal-airinterface is 0.58.	8M	CO4	L3
		(ii) When the optical power generated internally is 25% of the electric powersupplied, determine the external power efficiency.			
(OR)					
8	а	Explain about p-n photodiode with depletion and diffusion regions and also explainp-n photodiode output characteristics with neat sketches.	7M	CO4	L4
	b	Explain about Laser diode amplification	8M	CO4	L3

9	а	Explain about Raman-Nath and Bragg modulators.	8M	CO5	L4		
	b	Write about Electro-optic amplitude modulation	7M	CO5	L5		
(OR)							
	а	Discuss the terms :Birefringence, Electro-optic effect	8M	CO5	L4		
10	b	Write short notes on Electro optic Phase modulation and Amplitude modulation.	7M	CO5	L4		